

Incommensurate Antiferromagnetic Structure in NiO Observed by Electron Diffraction

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Neutron diffraction has been used to investigate antiferromagnetism since 1949. Here we show that antiferromagnetic reflections can also be seen in transmission electron diffraction patterns from NiO. In some regions the antiferromagnetic structure was incommensurate with the crystal so the magnetic unit cell need not be an exact doubling of the structural cell as is usually assumed. The diffraction patterns taken here came from regions as small as 10.5 nm and such patterns could be used to image the antiferromagnetic structure with a nanometre resolution.

Antiferromagnetic materials have opposed magnetic moments on adjacent atoms and so produce no external magnetic field. They were first identified in 1932 [1] and today their main application is for computer hard drive readers which use the exchange-bias effect [2]. The arrangement of the atomic magnetic moments can be deduced by recording diffraction patterns using radiation sensitive to the magnetic flux density between the atoms. Neutrons have a magnetic moment μ_n (of magnitude 9.65×10^{-27} Am²) and so feel a force $\mathbf{F}_n = \mu_n \cdot \nabla \mathbf{B}$ on passing through a region with flux density $\mathbf{B}$. Neutron diffraction was first used to detect antiferromagnetism in 1949 [3] and has since been used extensively to study the structure of antiferromagnets [4]. Electrons should also be sensitive to antiferromagnetism as they are charged particles (with charge $-e = -1.602 \times 10^{-19}$ C) and so experience a Lorentz force $\mathbf{F}_e = -e\mathbf{v} \times \mathbf{B}$ on passing through a B-field with a velocity $\mathbf{v}$. The effect of the Lorentz force is used extensively in electron microscopy to map B-fields in ferromagnets [5] but our literature survey found no evidence of its use to examine antiferromagnets.

Antiferromagnetic domains have been imaged before using transmission electron microscopy but these images did not use magnetic scattering but relied on the fact that the domains observed were also structural twins [6]. In *Electron Microscopy of Thin Crystals* [7] it states ‘it is not clear whether the periodicity in the spins [of an antiferromagnet] can give rise to observable diffraction effects [in a transmission electron diffraction pattern]’. Here we show that antiferromagnetic reflections can be observed in electron diffraction patterns and are about 10^4 times less intense compared with the structural Bragg peaks unlike neutron diffraction where both are of similar intensity [4].

The Lorentz force is the dominant force felt by electrons due to the magnetic flux density in the specimen at the energies used for transmission electron microscopy (300 keV here) as shown in Supp. Info. 1. Unlike neutrons, the force due to the electron’s dipole moment never dominates and at low energy, the exchange interaction dominates [8]. Low energy (32 eV) electron diffraction

patterns have been acquired from the first atomic layer of an antiferromagnet [9] using this effect.

The advantage of transmission electron microscopy is its potential to examine features of the antiferromagnetic structure such as domain walls at high resolution. The diffraction patterns taken here came from regions as small as 10.5 nm in diameter with a thickness of about 100 nm and a 1 nm resolution should be possible. For comparison, the resolution of neutron imaging [10] is 60 μ m, low energy electron diffraction [9] 10 nm and photoemission electron microscopy [11] 20 nm.

In this experiment we acquired electron diffraction patterns from single crystal NiO as it is readily available and its magnetic structure is well characterised as it was one of the first antiferromagnets investigated using neutron diffraction [12]. Its crystal structure is based on the face-centred cubic, sodium chloride structure [13] with a lattice parameter of $a = 4.18$ Å. Antiferromagnetic order occurs below the Néel temperature, $T_N = 523$ K and consists of the ferromagnetic alignment of the magnetic moments of the Ni ions in one set of (111)-type planes with the moments in alternate (111) planes being antiparallel resulting in a doubling of the periodicity of the crystal in this direction (see Supp. Info. 2). Experimental measurements of the magnetic moment give values between 1.77 and $2.2 \pm 0.2 \mu_B$ per Ni ion [14] and the usual picture is that the contribution to the magnetic moment from the orbital angular momentum of the electrons is quenched and each Ni²⁺ ion has its spin-only moment of $2 \mu_B$ although this is questioned in ref. [14].

Antiferromagnetic order is accompanied by a slight rhombohedral distortion [13] which compresses the lattice along the [111] axis normal the ferromagnetic (111) planes. This distortion does not lead to extra reflections in a diffraction pattern and throughout we follow the usual convention of using the cubic coordinates. In Supp. Info. 3, it is shown that if positions in reciprocal space of the structural Bragg reflections are denoted $\mathbf{G} = (hkl)$ and the antiferromagnetic modulation in the local magnetisation is written $\mathbf{M} = \mathbf{M}_0 \cos(2\pi \mathbf{q} \cdot \mathbf{r})$ (where $\mathbf{r}$ is a position vector, $\mathbf{q}$ is the wavevector of the modulation and $\mathbf{M}_0$ is the sublattice magnetisation), antiferromag-

netic reflections occur at positions $\mathbf{Q} = \mathbf{G} \pm \mathbf{q}$ in diffraction patterns acquired using radiation sensitive to magnetism. For NiO, h, k and l must all be odd or all even numbers as it is a face-centred crystal. The antiferromagnetic wavevector points in one of four possible $\{111\}$ directions and each will generate different antiferromagnetic reflections. For example, the lowest order reflections generated by $\mathbf{q} = \frac{1}{2}(111)$ will be $\mathbf{Q} = \pm\frac{1}{2}(111)$, $\pm\frac{1}{2}(11\bar{3})$, $\pm\frac{1}{2}(1\bar{3}1)$, $\pm\frac{1}{2}(\bar{3}11)$ but it will not generate $\frac{1}{2}(113)$ as there is no allowed structural reflection, $\mathbf{G}$, from which this could originate. Each antiferromagnetic reflection in NiO originates from two structural reflections so if $\mathbf{q}$ deviates from $\frac{1}{2}(111)$, each antiferromagnetic reflection will be split in two.

In the absence of an applied magnetic field, the magnetic moments of the Ni ions, $\boldsymbol{\mu}$, point in one of the three $\langle 11\bar{2} \rangle$ directions (called ‘easy axes’) which lie in the ferromagnetically aligned (111) planes [15] and Supp. Info. 4 lists the intensities of the low order antiferromagnetic reflections calculated in Supp. Info. 3 for different directions of $\boldsymbol{\mu}$.

When the direction of the antiferromagnetic order changes, there are two types of domain boundary: a twin (T-type) boundary occurs when the magnetic order changes to a different set of (111) planes and the accompanying distortion generates a crystallographic twin. The spin (S-type) domain boundary occurs where the same set of (111) planes remains ferromagnetic but the magnetic moments point in a different direction (see Supp. Info. 2).

In this experiment, the microscope was used in its normal operating mode where the objective lens applies a 2.8 T magnetic field to the sample parallel to the electron beam. In single crystal NiO, the spins flop above 1.54 T so it is likely that the spins have flopped here [16]. The spin flop realigns the spins so they remain in the same zone as $\mathbf{q}$ but point normal to the applied field [16] and so will be in the $[1\bar{1}0]$ -type directions listed in Supp. Info. 4. In addition, the spins will be canted in the direction of the field by an angle of 9° (calculated from the susceptibility measurements in ref. [17]). The spin flop is actually an advantage for the purpose of seeing antiferromagnetic $\mathbf{Q} = \frac{1}{2}(11\bar{1})$ -type reflections as they have maximum intensity when the magnetic moments are normal to the incoming beam and it avoids the possibility of the reflections being invisible because the magnetic moments are parallel to the beam. We shall soon conduct similar experiments with the sample in a field free condition.

In Supp. Info. 3, the phase object approximation is used to derive the following formula for the intensity of an antiferromagnetic reflection at position $\mathbf{Q}$ relative to the 000 beam:

$$\frac{I_{\mathbf{Q}}}{I_0} = \left(\frac{e}{2h} \frac{\mu_0 \mu_B}{\Omega} \frac{t}{Q} (\hat{\boldsymbol{\mu}} \times \hat{\mathbf{Q}}) \cdot \hat{\mathbf{z}} F(\mathbf{Q}) \right)^2 \quad (1)$$

where h is Planck’s constant, Ω is the unit cell volume and t is the specimen thickness. $\hat{\boldsymbol{\mu}}$ is a unit vector in the direction of the magnetic moments, $\hat{\mathbf{Q}}$ is a unit vector in the scattering direction and $\hat{\mathbf{z}}$ is a unit vector in the direction of the incident electron beam. The structure factor is given by $F(\mathbf{Q}) \equiv \sum_j n_j f_j(\mathbf{Q}) e^{2\pi i \mathbf{k} \cdot \mathbf{Q}_j}$ where the sum is over all the atoms in one unit cell and $f_j(\mathbf{Q})$ is the magnetic form factor for atom j . The form factor is the same as for neutron diffraction as the same electrons generate the flux density and we use those given in ref. [18]. The calculated intensity ratios are tabulated in Supp. Info. 4 for a 100 nm thick specimen in the $\langle 112 \rangle$ -type zone axes investigated here.

The NiO single crystals used in this experiment were supplied by Pi-Kem Ltd and of size $5 \times 5 \times 0.5$ mm with the largest surface being (111). They were prepared for electron microscopy by thinning in the $[111]$ direction by mechanical polishing followed by argon ion beam thinning using a Gatan Precision Ion Polishing System (PIPS). Electron microscopy was conducted at room temperature using a Philips CM300 transmission electron microscope equipped with a field-emission gun operated at 300 kV.

To image antiferromagnetic reflections, a double tilt holder was used to tilt to the $[112]$, $[121]$ and $[211]$ zone axes, each of which is at an angle of 19.5° to $[111]$. This ensured that antiferromagnetic reflections would be seen in at least one of these zone axes irrespective of the direction of $\mathbf{q}$.

Electron diffraction patterns were acquired using Ditabis imaging plates which have a high dynamic range of 2 million grey levels. They were not energy filtered to remove inelastic scattering as the post-column Gatan Imaging Filter on this microscope does not allow energy filtered images to be acquired on imaging plates although it would have been desirable. The patterns were acquired with exposures between 0.2 and 100 s at camera lengths of 740–3900 mm. The shortest exposure in which antiferromagnetic reflections could be seen was 0.24 s.

We first used polarised optical microscopy to visualise the rhombohedral (T-type) domains (Supp. Info. 5) which showed that they ranged in size from 2–80 μm . Fig. 1 shows an electron diffraction pattern from the $[211]$ zone axis exhibiting superlattice reflections at $\mathbf{Q} = \frac{1}{2}(\bar{1}11)$ and very faintly at $\frac{1}{2}(\bar{3}33)$ from a region of diameter 140 nm. Diffraction patterns taken in the same area from $[211]$ and $[121]$ showed no superlattice reflections indicating the region was a single antiferromagnetic domain with $\mathbf{q} = \frac{1}{2}(\bar{1}11)$.

Fig. 1 was taken with an exposure of 200 s and an identical pattern was taken with an exposure of 0.242 s to avoid saturating the 000 beam. This enabled the intensity ratio of the $\frac{1}{2}(\bar{1}11)$ reflection to the 000 beam to be measured as $(1.08 \pm 0.03) \times 10^{-4}$. The thickness was not measured but it was likely to be around 100 nm and it can be seen that the ratio is in the regime predicted

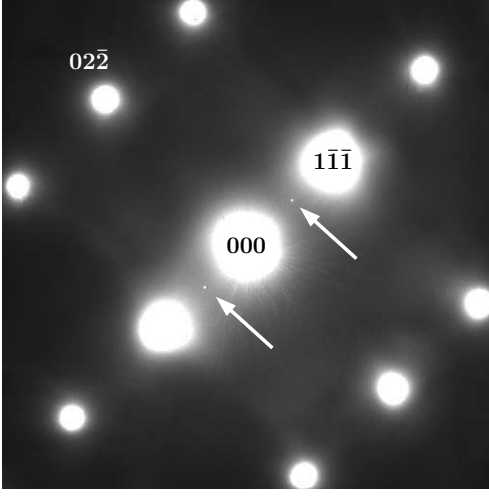


FIG. 1. Electron diffraction pattern taken from the $[211]$ zone axis with an exposure of 200 s showing antiferromagnetic reflections (indicated by arrows) at $\pm\frac{1}{2}(\bar{1}11)$ and very faintly at $\frac{1}{2}(\bar{3}33)$ taken from a region of diameter 140 nm.

in Supp. Info. 4. Eqn. (1) shows that the intensity ratio of $\frac{1}{2}(\bar{3}33)$ to $\frac{1}{2}(\bar{1}11)$ does not depend on thickness and it was measured as 0.043 ± 0.003 which agrees with the predicted value of 0.045 ± 0.004 for the spin-flopped configuration. The facts that the reflections appear in the right place, obey the correct diffraction conditions and have the right intensities show that these superlattice reflections originate from antiferromagnetism. We also note that the full-width-half-maximum of the antiferromagnetic reflections was the same as the structural reflections to an upper limit of 0.2% of $|g_{111}|$ showing the correlation length for the antiferromagnetic structure was greater than 120 nm (comparable with the size of the region from which the pattern was taken) indicating that the antiferromagnet had very good long-range order.

Diffraction patterns from other regions of the specimen showed reflections at $\mathbf{Q} = \frac{1}{2}(\bar{3}11)$ -type positions indicating that the antiferromagnetic wavevector was $\mathbf{q} = \frac{1}{2}(111)$, parallel to the thin direction of the crystal. Interestingly, all the $\mathbf{Q} = \frac{1}{2}(\bar{1}11)$ -type reflections we observed were sharp, single peaks but in contrast, the $\mathbf{Q} = \frac{1}{2}(\bar{3}11)$ -type reflections frequently showed a splitting indicating that the antiferromagnetic wavevector deviated from $\mathbf{q} = \frac{1}{2}(111)$. An example is shown in Fig. 2 where spots appear at $(-1.467, 0.519, 0.474)$ and $(-1.538, 0.482, 0.528)$ indicating a wavevector of $\mathbf{q} = (0.465, 0.482, 0.527)$ (with an error of ± 0.002 in each component).

More complicated splittings were seen in other regions and Fig. 3 shows enlargements of the $\frac{1}{2}(\bar{1}3\bar{1})$ -type reflections in the $[112]$ zone. Here there are two antiferromagnetic wavevectors present, $\mathbf{q}_1 = (0.492, 0.504, 0.502)$ and $\mathbf{q}_2 = (0.485, 0.471, 0.522)$ (with an error of ± 0.002 in each component). The intensity of all four of the split reflections is similar indicating that the magnetic moment

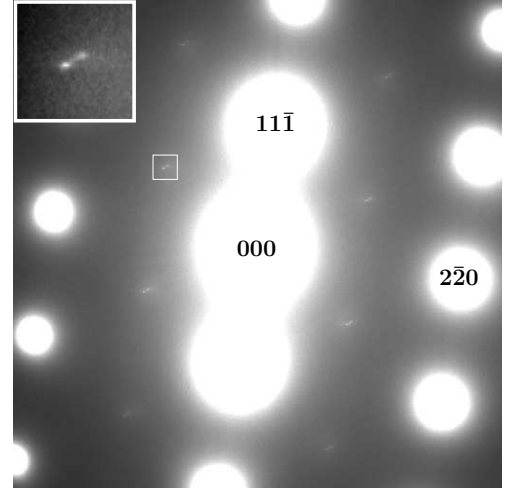


FIG. 2. Electron diffraction pattern taken from the $[112]$ zone axis from a region 820 nm in diameter with an exposure of 70 s showing split antiferromagnetic reflections at $\pm\frac{1}{2}(\bar{3}11)$ and $\pm\frac{1}{2}(\bar{1}3\bar{1})$, one of which is enlarged in the inset.

was either $[1\bar{1}0]$ in the probable case that the spins had flopped or $[11\bar{2}]$ if they lay along an easy axis. The other two possible easy directions are excluded as Supp. Info. 4 shows that in that case either $\frac{1}{2}(\bar{3}11)$ or $\frac{1}{2}(\bar{1}3\bar{1})$ would be two orders of magnitude dimmer than the other. Thus it is likely that the magnetic moments lie in the same direction for both the $\mathbf{q}_1$ and $\mathbf{q}_2$ domains and if so, they are neither T nor S domains but what we term ‘q-domains’ as the magnetic moments point in the same direction in each but the antiferromagnetic wavevector changes its direction and magnitude. q-domains are only possible for an incommensurate wavevector: both would be identical if the wavevector were commensurate.

In all of the diffraction patterns we recorded (about 50), the $\mathbf{Q} = \frac{1}{2}(11\bar{1})$ -type reflections arising from antiferromagnetic modulations with wavevectors $\mathbf{q}$ normal to the electron beam gave sharp, single peaks whereas the $\mathbf{Q} = \frac{1}{2}(11\bar{3})$ -type reflections which originated from $\mathbf{q} = \frac{1}{2}(111)$, parallel to the thin direction of the crystal, were frequently split indicating a modulation which was incommensurate with the structural lattice. The splitting of the $\mathbf{Q} = \frac{1}{2}(11\bar{3})$ -type reflections, $\Delta\mathbf{Q}$, ranged in magnitude from 0– $0.07a^*$ (where a^* is the reciprocal lattice vector) and there seems to be no restriction on the angle of $\Delta\mathbf{Q}$ with respect to the rest of the pattern.

It is not clear why the modulation parallel to the thin (~ 100 nm) direction of the crystal should sometimes be incommensurate whilst the modulation in other directions is commensurate. Presumably it is due either to the strain caused by ion thinning or the boundary condition of having free surfaces interacting with the strain which accompanies antiferromagnetism. It shows, however, that NiO can support an incommensurate antiferromagnetic structure. This is interesting because

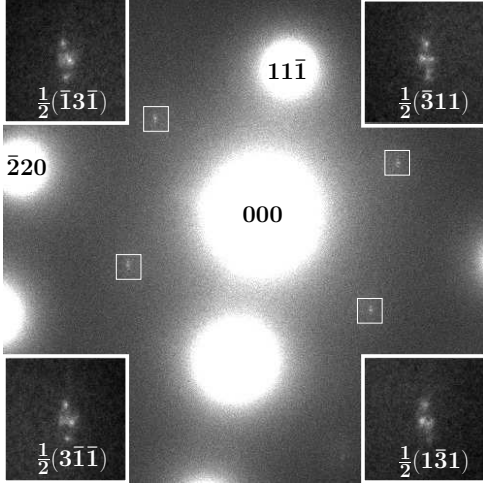


FIG. 3. Electron diffraction pattern from the $[112]$ zone axis taken from a region 820 nm in diameter with an exposure of 70 s showing enlargements of the split reflections at $\pm\frac{1}{2}(\bar{1}31)$ and $\pm\frac{1}{2}(\bar{3}11)$.

although incommensurate antiferromagnetism has been observed in many systems (chromium is a prototypical example) it is usually attributed to Fermi surface nesting [19] whereas antiferromagnetism in NiO is attributed to superexchange interactions between neighbouring Ni ions [20].

It would be advantageous to develop a technique for imaging antiferromagnetism using electron microscopy. We have attempted dark field imaging but the images have been dominated by diffuse scattering as the antiferromagnetic reflections are so weak. We have also attempted high resolution imaging which would give information on an atomic scale but with no success so far. We shall soon be conducting simulations to ascertain the effects of antiferromagnetism on high resolution images.

It seems that the most promising imaging technique is spatially resolved diffraction where a narrow, near-parallel electron beam is rastered across the specimen and a diffraction pattern recorded at each point. An image can be built up by plotting the intensity of particular reflections as a function of position. This technique is not standard on most microscopes and its implementation will require modifying the software on our microscope. In Supp. Info. 6 we show that diffraction patterns showing antiferromagnetic reflections can be obtained from 10.5 nm diameter regions. Tao *et al.* [21] have used this technique to image charge-ordered domains in $\text{La}_{0.55}\text{Ca}_{0.45}\text{MnO}_3$ and have achieved a resolution of 1.7 nm.

In summary, we have shown that antiferromagnetic reflections can be observed in transmission electron diffraction patterns taken from NiO with 300 keV electrons with an intensity $\sim 10^4$ times less intense than the structural reflections. We give a mathematical model which pre-

dicts the intensities of the antiferromagnetic reflections and agrees with the observations made here, allowing deductions to be made about the direction of the magnetic moments. We found that when the antiferromagnetic modulation ran parallel to the $[111]$ direction in which the crystal had been thinned to ~ 100 nm, the antiferromagnetic modulation could be incommensurate with the structural lattice but that for other directions the modulation was commensurate. The diffraction patterns taken here were from regions as small as 10.5 nm in diameter and such patterns could be used to image the antiferromagnetic structure using spatially resolved electron diffraction with a resolution of around 1 nm.

SUPPLEMENTARY INFORMATION 1: ESTIMATE OF THE FORCE ON AN ELECTRON AS IT PASSES THROUGH AN ANTIFERROMAGNET

For transmission electron microscopy, the Lorentz force is about 500 times larger than the force the electron feels due to its magnetic dipole moment as the following estimate shows. The maximum Lorentz force, $\mathbf{F}_e = -e\mathbf{v} \times \mathbf{B}$ felt by an electron passing through an antiferromagnet is about 2.4×10^{-11} N (using $v = 2.3 \times 10^8 \text{ ms}^{-1}$ for 300 keV electrons and $B = \mu_0 M_0 = 0.64$ T where M_0 is the sublattice magnetisation for NiO) whereas the force due to the electron's magnetic moment is $\mathbf{F}_\mu = \boldsymbol{\mu}_e \cdot \nabla \mathbf{B}$ and has a maximum value of $F_\mu \approx \mu_B(2B/d) = 4.9 \times 10^{-14}$ N (where $d = 2.4 \text{ \AA}$ is the spacing between the (111) planes of antiparallel spins in NiO). A similar estimate shows that the energy of the electron beam would need to be 0.7 eV before the Lorentz and dipolar forces are equal.

In fact, unlike neutron diffraction, the dipolar force never dominates and at low energies, the dominant force is from the exchange interaction arising from the fact that the electrons in the beam and the antiferromagnet are identical particles as discussed by DeWames and Vredevoe [8]. The exchange interaction is larger than the dipole interaction by a factor of the rest mass energy of the electron (511 keV) divided by the kinetic energy of an electron in the beam [8]. This ratio is 1.7 at 300 keV and so it is the Lorentz interaction which dominates at high energies.

Low energy (32 eV) electron diffraction patterns have been acquired from the first atomic layer of an antiferromagnet by Menon *et al.* [9] and here the exchange interaction dominates the scattering process as it is about 16000 times greater than the dipolar interaction and 2300 times greater than the Lorentz force. Menon *et al.* [9] have used these diffraction patterns to image antiferromagnetic domains in the first atomic layer of the sample with a resolution of 10 nm.

SUPPLEMENTARY INFORMATION 2: ANTIFERROMAGNETIC DOMAINS

In NiO, the magnetic moments are aligned ferromagnetically along one set of $\{111\}$ planes with the moments in alternating planes being antiparallel as shown in Fig. 4(a). There are two types of antiferromagnetic domain boundary: a twin (T-type) boundary occurs when the magnetic order changes to a different set of $\{111\}$ planes and the accompanying distortion generates a crystallographic twin (Fig. 4(b)). The spin (S-type) domain boundary occurs when the same set of $\{111\}$ planes remains ferromagnetic but the magnetic moments point in a different direction (Fig. 4(c)).

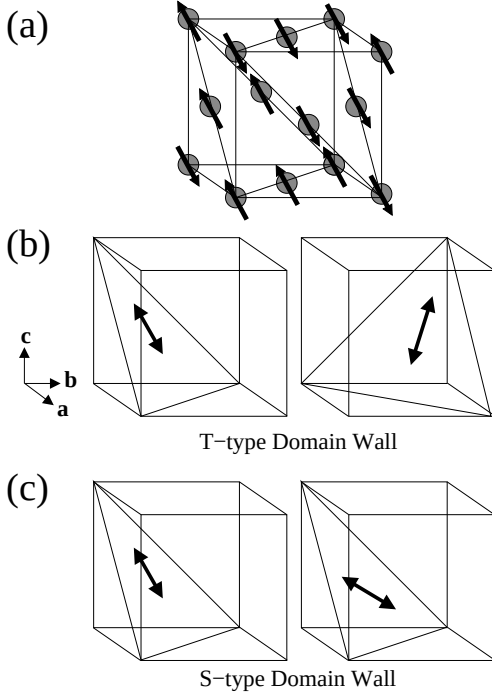


FIG. 4. (a) Arrangement of Ni ions and spins in one unit cell of NiO showing the ferromagnetic alignment in the $\{111\}$ planes. (b) Changes in the direction of the magnetic moments due to a T-type and (c) an S-type domain boundary. The double headed arrows indicate the direction of the magnetic moments in the ferromagnetic $\{111\}$ planes shown.

SUPPLEMENTARY INFORMATION 3: THEORY OF ELECTRON DIFFRACTION FROM AN ANTIFERROMAGNET

Here we calculate the appearance of an electron diffraction pattern from an antiferromagnet and estimate the intensities of the antiferromagnetic reflections. To do this, we arrange Cartesian coordinates so that the electron beam is travelling in the z -direction before it hits the specimen and then the wavefunction of the electron

$\psi(x, y, z)$ at any point can be found using the Schrödinger equation for fast electrons [22, 23]:

$$\frac{\partial \psi}{\partial z} = i \frac{\lambda}{4\pi} \nabla_{xy}^2 \psi + i \left(C_E V - \frac{2\pi e}{h} A_z \right) \psi - \frac{\lambda e}{h} \mathbf{A} \cdot \nabla \psi \quad (2)$$

where $V(x, y, z)$ is the electrostatic potential, $\mathbf{A}(x, y, z)$ is the magnetic vector potential, λ the electron wavelength and $C_E = \frac{2\pi e}{\lambda} \left(\frac{E + mc^2}{E(E + 2mc^2)} \right)$ where E is the kinetic energy of the electrons, m the rest mass of the electrons, λ their wavelength and c is the speed of light in a vacuum.

This equation is used throughout electron microscopy to simulate images and diffraction patterns but usually with only the electrostatic terms. Here we have retained the magnetic terms and inserting a suitable expression for the vector potential from an antiferromagnet would allow very accurate simulations of images and diffraction patterns. This equation can only be solved iteratively, however, usually using the multislice or Bloch wave approaches [22] and to give an analytic solution, we make the phase object approximation where only the second term on the right hand side equation 2 is retained. This approximation is valid for very thin specimens but gives a physical insight into the situation and provides an estimate of the intensities expected in a diffraction pattern. Having made this approximation, equation 2 is readily solved to give the wavefunction of the electron as it emerges from a sample of thickness t (called the ‘exit-plane wavefunction’) as $\psi(x, y) = e^{i\phi(x, y)}$ where

$$\phi(x, y) = \int_{-t/2}^{t/2} \left(C_E V(x, y, z) - \frac{2\pi e}{h} A_z(x, y, z) \right) dz \quad (3)$$

(We have assumed that both potentials are zero outside the specimen which is very reasonable for an antiferromagnet.)

We now show that the magnetic contribution to the phase is small by taking the case where the antiferromagnetic wavevector $\mathbf{q}$ points in the x -direction and the flux density oscillates in y . This will give the largest possible phase shift as the B-field is normal to the electron beam direction z . If we write $B_y = B_0 \cos(2\pi q_x x)$, a suitable vector potential is $A_z = -(B_0/2\pi q_x) \sin(2\pi q_x x)$ and this gives a phase shift $\phi(x) = (eB_0 t/hq_x) \sin(2\pi q_x x)$. For NiO, $B_0 = 0.64$ T and $q = \sqrt{3}/2a = 0.207 \text{ \AA}^{-1}$, the maximum phase shift for a 100 nm thick specimen is 7.5×10^{-3} radians.

Returning to the general case, this means that we can make the weak phase object approximation for the magnetic contribution to the phase, $\exp[-i2\pi e/h \int_{-\infty}^{\infty} A_z dz] \approx 1 - i2\pi e/h \int_{-\infty}^{\infty} A_z dz$ and if the electrostatic contribution to the wavefunction is denoted $\psi_V \equiv \int_{-\infty}^{\infty} \exp[iC_E V(x, y, z) dz]$, the exit-plane wavefunction is

$$\begin{aligned}\psi(x, y) &= \psi_V \left(1 - i \frac{2\pi e}{h} \int_{-t/2}^{t/2} A_z dz \right) \\ &= \psi_V \left(1 - i \frac{2\pi e}{h} \int_{-\infty}^{\infty} A_z h(z) dz \right) \quad (4)\end{aligned}$$

where $h(z)$ is a top hat function which is 1 for $-t/2 < z < t/2$ and zero otherwise.

The diffraction pattern is the squared modulus of the Fourier transform of the exit plane wavefunction, $|\Psi(k_x, k_y)|^2$, and so, using the Fourier transform convention $\Psi(\mathbf{k}) = \int_{-\infty}^{\infty} \psi(\mathbf{r}) e^{2\pi i \mathbf{k} \cdot \mathbf{r}} d^2 \mathbf{r}$, we obtain

$$\begin{aligned}\Psi(k_x, k_y) &= \Psi_V * \left(\delta(k_x) \delta(k_y) - i \frac{2\pi e}{h} \right. \\ &\quad \times \left. \left(\tilde{A}_z(k_x, k_y, k_z) * \text{sinc}(\pi k_z t) \right)_{k_z=0} \right) \quad (5)\end{aligned}$$

where $\tilde{A}_z$ denotes the three dimensional Fourier transform of A_z , $\text{sinc}(X) \equiv \sin(X)/X$, $*$ denotes a convolution and we have made use of the convolution and Fourier projection theorems.

We now calculate the magnetic vector potential for an antiferromagnet basing our method on that used to derive the intensities for neutron diffraction described in ref [24]. The result could be used in equation 2 but here we apply it for the phase object approximation. If we assume that the contribution from the orbital angular momentum of the electrons in the antiferromagnet is quenched, the magnetic vector potential can be found by summing the fields due to the magnetic moments generated by the spin of the unpaired electrons on each atom. A single electron at position $\mathbf{R}_i$ with magnetic moment $\boldsymbol{\mu}_i$ will generate a vector potential at position $\mathbf{r}$ of

$$\mathbf{A}_i(\mathbf{r}) = \frac{\mu_0}{4\pi} \frac{\boldsymbol{\mu}_i \times (\mathbf{r} - \mathbf{R}_i)}{|\mathbf{r} - \mathbf{R}_i|^3} = \frac{\mu_0}{4\pi} \frac{\boldsymbol{\mu}_i \times \mathbf{r}}{r^3} * \delta(\mathbf{r} - \mathbf{R}_i) \quad (6)$$

The vector potential for the entire crystal is then the sum over all the unpaired electrons

$$\mathbf{A}(\mathbf{r}) = \sum_i \frac{\mu_0}{4\pi} \frac{\boldsymbol{\mu}_i \times \mathbf{r}}{r^3} * \delta(\mathbf{r} - \mathbf{R}_i) \quad (7)$$

For a simple antiferromagnet where all the electron spins are collinear, we can write $\boldsymbol{\mu}_i = \hat{\boldsymbol{\mu}} \mu_i$ where $\hat{\boldsymbol{\mu}}$ is a unit vector pointing in the direction of the magnetic moment and μ_i expresses the magnitude and sign of the moment. Then

$$\mathbf{A}(\mathbf{r}) = \frac{\mu_0}{4\pi} \frac{\hat{\boldsymbol{\mu}} \times \mathbf{r}}{r^3} * \sum_i \mu_i \delta(\mathbf{r} - \mathbf{R}_i) \quad (8)$$

We recognise the last term as the local magnetisation, $M(\mathbf{r})$ so we can write:

$$\mathbf{A}(\mathbf{r}) = \frac{\mu_0}{4\pi} \frac{\hat{\boldsymbol{\mu}} \times \mathbf{r}}{r^3} * M(\mathbf{r}) \quad (9)$$

The magnetisation is the product of the electron number density and the magnetic moment of each electron $M(\mathbf{r}) = \rho(\mathbf{r})\mu(\mathbf{r})$. To model an antiferromagnet, we allow the magnetisation to vary depending on its position in the crystal. For NiO, this is conventionally done by using a ‘magnetic unit cell’ which is twice the size of the structural unit cell in each of the a , b and c directions and reversing the sign of $\boldsymbol{\mu}$ on alternating (111) planes [12]. Instead, we use the same unit cell as the structural unit cell but allow the magnetisation to vary as $M(\mathbf{r}) = \rho_0(\mathbf{r})\mu_B \cos(2\pi \mathbf{q} \cdot \mathbf{r})$ where $\rho_0(\mathbf{r})$ is the electron number density in the absence of the modulation and μ_B is the size of the magnetic moment on each electron, the Bohr Magneton. This represents the lowest-order Fourier component of an antiferromagnetic modulation and this approach has the advantages that the wavevector of the modulation, $\mathbf{q}$, need not be commensurate with the atomic lattice and that it can have any direction.

It turns out to be convenient to write the number density of electrons in terms of the number density of electrons for one atom. If the atom is labelled j and the unpaired electron density with the origin at the centre of the atom is denoted $\rho_j(\mathbf{r})$, we can write:

$$\begin{aligned}\rho_0(\mathbf{r}) &= \sum_n \sum_j \rho_j(\mathbf{r} - \mathbf{R}_n - \mathbf{R}_j) \\ &= \sum_n \sum_j \rho_j(\mathbf{r}) * \delta(\mathbf{r} - \mathbf{R}_n - \mathbf{R}_j) \quad (10)\end{aligned}$$

where $\mathbf{R}_j$ is the position of atom j within its unit cell and $\mathbf{R}_n$ is the position of the unit cell within the crystal. Thus, the vector potential becomes:

$$\begin{aligned}\mathbf{A}(\mathbf{r}) &= \frac{\mu_0 \mu_B}{4\pi} \frac{\hat{\boldsymbol{\mu}} \times \mathbf{r}}{r^3} * \sum_n \sum_j (\rho_j(\mathbf{r}) * \delta(\mathbf{r} - \mathbf{R}_n - \mathbf{R}_j)) \\ &\quad \times \cos(2\pi \mathbf{q} \cdot \mathbf{r}) \quad (11)\end{aligned}$$

The z -component of the vector potential can be selected by multiplying by a unit vector in the z -direction, $\hat{\mathbf{z}}$ thus:

$$\begin{aligned}A_z(\mathbf{r}) &= \frac{\mu_0 \mu_B}{4\pi} \frac{\hat{\boldsymbol{\mu}} \times \mathbf{r}}{r^3} \cdot \hat{\mathbf{z}} * \sum_n \sum_j (\rho_j(\mathbf{r}) * \delta(\mathbf{r} - \mathbf{R}_n - \mathbf{R}_j)) \\ &\quad \times \cos(2\pi \mathbf{q} \cdot \mathbf{r}) \quad (12)\end{aligned}$$

The Fourier transform of this expression is

$$\begin{aligned}\tilde{A}_z(\mathbf{k}) &= \frac{\mu_0}{4\pi k} (\hat{\boldsymbol{\mu}} \times \hat{\mathbf{k}}) \cdot \hat{\mathbf{z}} \sum_n \sum_j (\tilde{\rho}_j(\mathbf{k}) e^{2\pi i \mathbf{k} \cdot \mathbf{R}_n} e^{2\pi i \mathbf{k} \cdot \mathbf{R}_j}) \\ &\quad * \frac{\mu}{2} (\delta(\mathbf{k} - \mathbf{q}) + \delta(\mathbf{k} + \mathbf{q}))\end{aligned}\quad (13)$$

where we have used the result that the Fourier transform of $\left[\frac{\mathbf{r}}{r^3}\right]$ is $-2\left(\frac{\mathbf{k}}{k^3}\right)$ and introduced a unit vector so that $\mathbf{k} = k\hat{\mathbf{k}}$. Recognising that the Fourier transform of the density of unpaired electrons is n_j , the number of unpaired electrons associated with atom j multiplied by the magnetic form factor, $f_j(k)$ (identical to that used in neutron diffraction) we can now write

$$\begin{aligned}\tilde{A}_z(\mathbf{k}) &= -\frac{\mu_0\mu_B}{4\pi k} (\hat{\boldsymbol{\mu}} \times \hat{\mathbf{k}}) \cdot \hat{\mathbf{z}} \sum_j n_j f_j(\mathbf{k}) e^{2\pi i \mathbf{k} \cdot \mathbf{R}_j} \sum_n e^{2\pi i \mathbf{k} \cdot \mathbf{R}_n} \\ &\quad * (\delta(\mathbf{k} - \mathbf{q}) + \delta(\mathbf{k} + \mathbf{q}))\end{aligned}\quad (14)$$

Using the result that $\sum_n e^{2\pi i \mathbf{k} \cdot \mathbf{R}_n} = \frac{1}{\Omega} \sum_{\mathbf{G}} \delta(\mathbf{k} - \mathbf{G})$ where $\mathbf{G}$ is a reciprocal lattice vector of the structural unit cell and Ω is the unit cell volume, we obtain

$$\begin{aligned}\tilde{A}_z(\mathbf{k}) &= -\frac{\mu_0\mu_B}{4\pi k} (\hat{\boldsymbol{\mu}} \times \hat{\mathbf{k}}) \cdot \hat{\mathbf{z}} \sum_j n_j f_j(\mathbf{k}) e^{2\pi i \mathbf{k} \cdot \mathbf{R}_j} \\ &\quad \times \frac{1}{\Omega} \sum_{\mathbf{Q}} \delta(\mathbf{k} - \mathbf{Q})\end{aligned}\quad (15)$$

where $\mathbf{Q} = \mathbf{G} \pm \mathbf{q}$. So the Fourier transform of the exit-plane wavefunction is

$$\begin{aligned}\Psi(k_x, k_y) &= \Psi_V(k_x, k_y) * \left(\delta(k_x) \delta(k_y) \right. \\ &\quad \left. + i \frac{e}{2h} \frac{\mu_0\mu_B}{\Omega} \frac{t}{k} (\hat{\boldsymbol{\mu}} \times \hat{\mathbf{k}}) \cdot \hat{\mathbf{z}} \sum_j n_j f_j(\mathbf{k}) e^{2\pi i \mathbf{k} \cdot \mathbf{R}_j} \right. \\ &\quad \left. \times \sum_{\mathbf{Q}} \delta(k_x - Q_x) \delta(k_y - Q_y) \text{sinc}(\pi Q_z t) \right)\end{aligned}\quad (16)$$

Thus if the structural Bragg reflections occur at $\mathbf{G}$, the antiferromagnetic reflections occur at $\mathbf{Q} = \mathbf{G} \pm \mathbf{q}$. It can be seen that the scattering amplitude is proportional to a geometric factor $G_e(\mathbf{k}) = ((\hat{\boldsymbol{\mu}} \times \hat{\mathbf{k}}) \cdot \hat{\mathbf{z}}/k)$ multiplied by the structure factor for magnetic scattering, $F(\mathbf{k}) \equiv \sum_j n_j f_j(\mathbf{k}) e^{2\pi i \mathbf{k} \cdot \mathbf{R}_j}$. For neutron diffraction, there is a similar expression where the structure factor is the same but the geometric factor $G_n(\mathbf{k}) \equiv |\hat{\mathbf{k}} \times \boldsymbol{\mu} \times \hat{\mathbf{k}}|$.

We use this expression for $\Psi(k_x, k_y)$ to calculate the intensities of the antiferromagnetic reflections $I_{\mathbf{Q}}$ in an electron diffraction pattern for a 100 nm thick specimen relative to the 000 beam, I_0 . The results are shown in table I for various directions of $\boldsymbol{\mu}$. In its construction we made the further approximation that the 000 beam is

much stronger than the other structural Bragg peaks (in the diffraction patterns acquired here it was typically 3–4 times more intense than the neighbouring peaks) so that as far as magnetic scattering is concerned, Ψ_V is simply a delta function at 000 and the intensity ratios are given by

$$\frac{I_{\mathbf{Q}}}{I_0} = \left(\frac{e}{2h} \frac{\mu_0\mu_B}{\Omega} \frac{t}{Q} (\hat{\boldsymbol{\mu}} \times \hat{\mathbf{Q}}) \cdot \hat{\mathbf{z}} F(\mathbf{Q}) \right)^2 \quad (17)$$

SUPPLEMENTARY INFORMATION 4: TABLE OF CALCULATED INTENSITIES OF ANTIFERROMAGNETIC REFLECTIONS

Table I gives the intensities of the antiferromagnetic reflections for 100 nm thick NiO for the [112]-type zone axes investigated in this experiment calculated according to the method in Supp. Info. 3. The form factors used in its construction were $f\left(\frac{1}{2}(111)\right) = 0.92 \pm 0.03$, $f\left(\frac{1}{2}(113)\right) = 0.82 \pm 0.02$ and $f\left(\frac{1}{2}(333)\right) = 0.58 \pm 0.02$ derived using neutron diffraction in ref [18]. The symbols used are as follows: $\mathbf{z}$ is the direction of the electron beam relative to the crystal, $\mathbf{q}$ is the wavevector of the antiferromagnetic modulation, $\mathbf{Q}$ gives the reciprocal-space coordinates of the reflection being examined, $\boldsymbol{\mu}$ gives the direction of the magnetic moments and $I_{\mathbf{Q}}/I_0$ gives the intensity of the reflection relative to the central beam. The intensity is given both for the case that $\boldsymbol{\mu}$ points in one of the [112]-type easy directions and for the $[1\bar{1}0]$ -type ‘flopped’ directions.

TABLE I. Antiferromagnetic Reflections in an Electron Diffraction from 100 nm thick NiO.

z	q	Q	μ	I_Q/I_0
[211]	$\frac{1}{2}(\bar{1}11)$	$\frac{1}{2}(\bar{1}11)$	[211]	0
			[12 $\bar{1}$]	$(1.40 \pm 0.08) \times 10^{-4}$
			[1 $\bar{1}2$]	$(1.40 \pm 0.08) \times 10^{-4}$
			[01 $\bar{1}$]	$(1.88 \pm 0.12) \times 10^{-4}$
		$\frac{1}{2}(\bar{3}33)$	[211]	0
			[12 $\bar{1}$]	$(6.0 \pm 0.4) \times 10^{-6}$
			[1 $\bar{1}2$]	$(6.0 \pm 0.4) \times 10^{-6}$
	$\frac{1}{2}(111)$	$\frac{1}{2}(11\bar{3})$	[01 $\bar{1}$]	$(8.4 \pm 0.4) \times 10^{-6}$
			$\bar{2}11$	$(2.64 \pm 0.12) \times 10^{-5}$
			[12 $\bar{1}$]	$(2.96 \pm 0.12) \times 10^{-5}$
			[1 $\bar{1}2$]	$(1.04 \pm 0.04) \times 10^{-7}$
		$\frac{1}{2}(1\bar{3}1)$	[01 $\bar{1}$]	$(1.12 \pm 0.04) \times 10^{-5}$
			$\bar{2}11$	$(2.64 \pm 0.12) \times 10^{-5}$
			[12 $\bar{1}$]	$(1.04 \pm 0.04) \times 10^{-7}$
	$\frac{1}{2}(111)$	$\frac{1}{2}(11\bar{3})$	[1 $\bar{1}2$]	$(2.96 \pm 0.12) \times 10^{-5}$
			[01 $\bar{1}$]	$(1.12 \pm 0.04) \times 10^{-5}$
		$\frac{1}{2}(\bar{3}11)$	$\bar{2}11$	$(1.04 \pm 0.4) \times 10^{-7}$
			[12 $\bar{1}$]	$(2.64 \pm 0.12) \times 10^{-5}$
			[1 $\bar{1}2$]	$(2.96 \pm 0.16) \times 10^{-5}$
		$\frac{1}{2}(\bar{3}11)$	[01 $\bar{1}$]	$(1.12 \pm 0.04) \times 10^{-5}$
[121]	$\frac{1}{2}(1\bar{1}1)$	$\frac{1}{2}(1\bar{1}1)$	[21 $\bar{1}$]	$(1.40 \pm 0.08) \times 10^{-4}$
			[121]	0
			[1 $\bar{1}2$]	$(1.40 \pm 0.08) \times 10^{-4}$
			[10 $\bar{1}$]	$(1.88 \pm 0.12) \times 10^{-4}$
		$\frac{1}{2}(\bar{3}\bar{3}3)$	[21 $\bar{1}$]	$(6.0 \pm 0.4) \times 10^{-6}$
			[121]	0
			[1 $\bar{1}2$]	$(6.0 \pm 0.4) \times 10^{-6}$
	$\frac{1}{2}(111)$	$\frac{1}{2}(11\bar{3})$	[10 $\bar{1}$]	$(8.4 \pm 0.4) \times 10^{-6}$
			$\bar{2}11$	$(2.96 \pm 0.16) \times 10^{-5}$
			[12 $\bar{1}$]	$(2.64 \pm 0.12) \times 10^{-5}$
			[1 $\bar{1}2$]	$(1.04 \pm 0.04) \times 10^{-7}$
		$\frac{1}{2}(\bar{3}11)$	[01 $\bar{1}$]	$(1.12 \pm 0.04) \times 10^{-5}$
			$\bar{2}11$	$(1.04 \pm 0.4) \times 10^{-7}$
			[12 $\bar{1}$]	$(2.64 \pm 0.12) \times 10^{-5}$
	$\frac{1}{2}(111)$	$\frac{1}{2}(\bar{3}11)$	[1 $\bar{1}2$]	$(2.96 \pm 0.16) \times 10^{-5}$
			[01 $\bar{1}$]	$(1.12 \pm 0.04) \times 10^{-5}$
		$\frac{1}{2}(\bar{3}11)$	$\bar{2}11$	$(1.04 \pm 0.4) \times 10^{-7}$
			[12 $\bar{1}$]	$(2.64 \pm 0.12) \times 10^{-5}$
			[1 $\bar{1}2$]	$(2.96 \pm 0.16) \times 10^{-5}$
		$\frac{1}{2}(\bar{3}11)$	[01 $\bar{1}$]	$(1.12 \pm 0.04) \times 10^{-5}$
[112]	$\frac{1}{2}(11\bar{1})$	$\frac{1}{2}(11\bar{1})$	[2 $\bar{1}1$]	$(1.40 \pm 0.08) \times 10^{-4}$
			[121]	$(1.40 \pm 0.08) \times 10^{-4}$
			[112]	0
			[1 $\bar{1}0$]	$(1.88 \pm 0.12) \times 10^{-4}$
		$\frac{1}{2}(33\bar{3})$	[2 $\bar{1}1$]	$(6.0 \pm 0.4) \times 10^{-6}$
			[121]	$(6.0 \pm 0.4) \times 10^{-6}$
			[112]	0
	$\frac{1}{2}(111)$	$\frac{1}{2}(\bar{3}11)$	[1 $\bar{1}0$]	$(8.4 \pm 0.4) \times 10^{-6}$
			$\bar{2}11$	$(1.04 \pm 0.04) \times 10^{-7}$
			[12 $\bar{1}$]	$(2.96 \pm 0.16) \times 10^{-5}$
			[1 $\bar{1}2$]	$(2.64 \pm 0.12) \times 10^{-5}$
		$\frac{1}{2}(1\bar{3}1)$	[1 $\bar{1}0$]	$(1.12 \pm 0.04) \times 10^{-5}$
			$\bar{2}11$	$(2.96 \pm 0.16) \times 10^{-5}$
			[12 $\bar{1}$]	$(1.04 \pm 0.04) \times 10^{-7}$
	$\frac{1}{2}(111)$	$\frac{1}{2}(\bar{3}11)$	[1 $\bar{1}2$]	$(2.64 \pm 0.12) \times 10^{-5}$
			[1 $\bar{1}0$]	$(1.12 \pm 0.04) \times 10^{-5}$
		$\frac{1}{2}(1\bar{3}1)$	$\bar{2}11$	$(2.96 \pm 0.16) \times 10^{-5}$
			[12 $\bar{1}$]	$(1.04 \pm 0.04) \times 10^{-7}$
			[1 $\bar{1}2$]	$(2.64 \pm 0.12) \times 10^{-5}$
		$\frac{1}{2}(1\bar{3}1)$	[1 $\bar{1}0$]	$(1.12 \pm 0.04) \times 10^{-5}$

SUPPLEMENTARY INFORMATION 5: OPTICAL MICROSCOPY

We assessed the size of the antiferromagnetic domains using optical microscopy. Fig. 5 is a transmission optical micrograph taken with crossed polars. This does not pick out the antiferromagnetic domains *per se* but the twins associated with each antiferromagnetic domain so only the T-type domains are visible. (Kondoh *et al.* [25] have reported that S-domains can also be imaged with optical microscopy due to their associated lattice strain but the contrast is much fainter.) This shows that the sizes of the T-domains range from 2–80 μm .

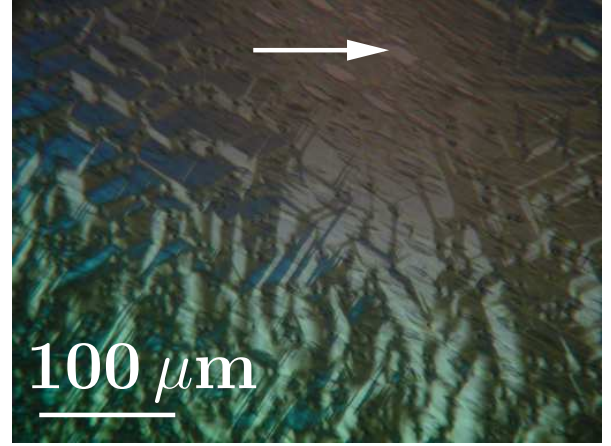


FIG. 5. Transmission optical micrograph taken with crossed polars looking down the [111] zone axis. The arrow shows a hole caused by ion-beam irradiation around which was the electron transparent material used for transmission electron microscopy.

SUPPLEMENTARY INFORMATION 6: SMALL-AREA ELECTRON DIFFRACTION

Fig. 6(a) shows a standard selected-area electron diffraction pattern from a 820 nm diameter region showing antiferromagnetic reflections at $\pm\frac{1}{2}(1\bar{3}1)$ and $\pm\frac{1}{2}(\bar{3}11)$. Fig. 6(b) demonstrates that it is possible to take electron diffraction patterns showing antiferromagnetic reflections from regions a few nanometres in size. The pattern was taken using a converged electron beam limited with a 5 μm condenser aperture. This gave a probe of full-width-half-maximum 10.5 nm and a convergence angle of 0.8 mrad.

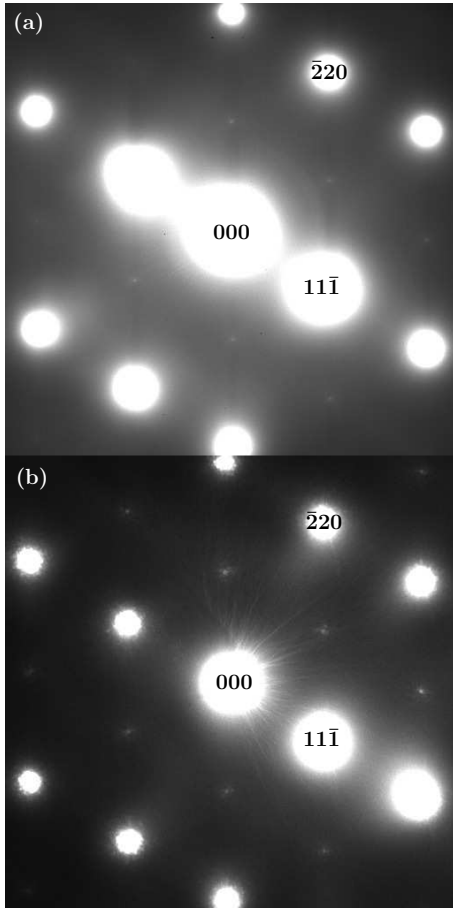


FIG. 6. Electron diffraction patterns from the $[112]$ zone axis. (a) is from an 820 nm diameter region of the specimen taken with an exposure of 70 s, (b) is from a 10.5 nm diameter region within the area of (a) taken with an exposure of 100 s. Both patterns show antiferromagnetic reflections at $\pm\frac{1}{2}(\bar{1}\bar{3}1)$ and $\pm\frac{1}{2}(\bar{3}11)$.

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